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# HSM276S

Silicon Schottky Barrier Diode for Balanced Mixer

# HITACHI

ADE-208-039E (Z)

Rev. 5  
Jul. 1998

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## Features

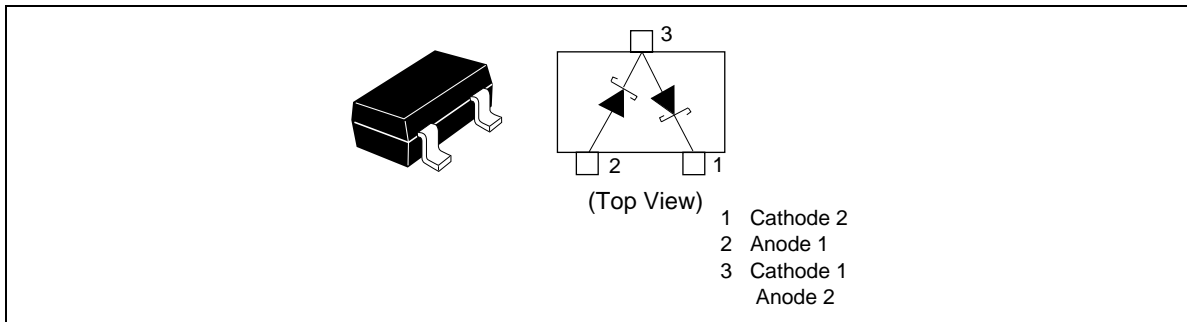
- High forward current, Low capacitance.
- HSM276S which is interconnected in series configuration is designed for balanced mixer use.
- MPAK package is suitable for high density surface mounting and high speed assembly.

## Ordering Information

Type No.	Laser Mark	Package Code
HSM276S	C2	MPAK

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## Outline



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## HSM276S

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### Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	$V_R$	3	V
Average rectified current	$I_O$	30	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

### Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	$V_R$	3.0	—	—	V	$I_R = 1 \text{ mA}$
Reverse current	$I_R$	—	—	50	$\mu\text{A}$	$V_R = 0.5\text{V}$
Forward current	$I_F$	35	—	—	mA	$V_F = 0.5\text{V}$
Capacitance	C	—	—	0.90	pF	$V_R = 0.5\text{V}, f = 1 \text{ MHz}$
Capacitance deviation	$\Delta C$	—	—	0.10	pF	$V_R = 0.5\text{V}, f = 1 \text{ MHz}$
ESD-Capability <sup>1</sup>	—	30	—	—	V	C=200pF , Both forward and reverse direction 1 pulse.

Notes 1. Failure criterion ;  $I_R \geq 100\mu\text{A}$  at  $V_R = 0.5 \text{ V}$

Main Characteristic

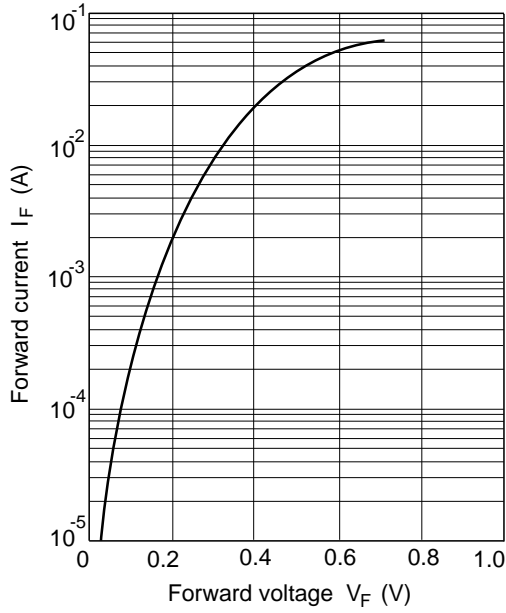


Fig.1 Forward current Vs. Forward voltage

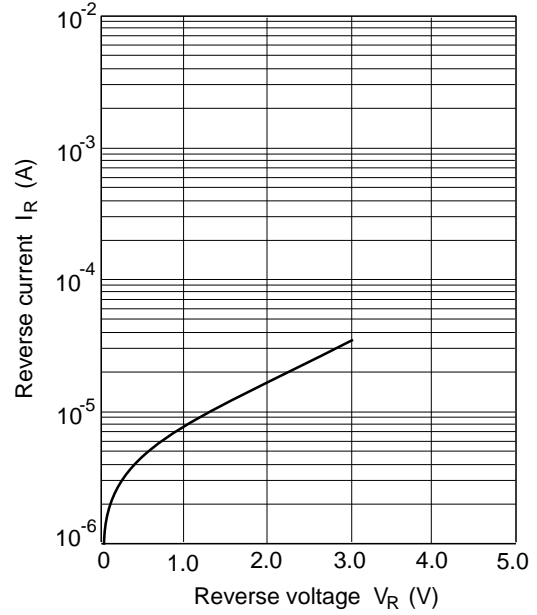


Fig.2 Reverse current Vs. Reverse voltage

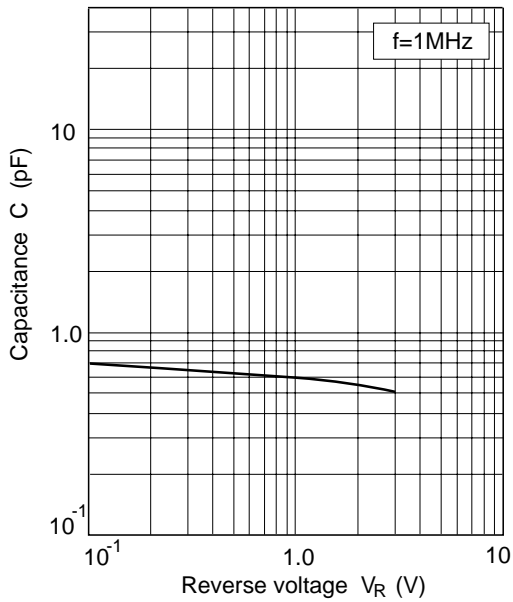
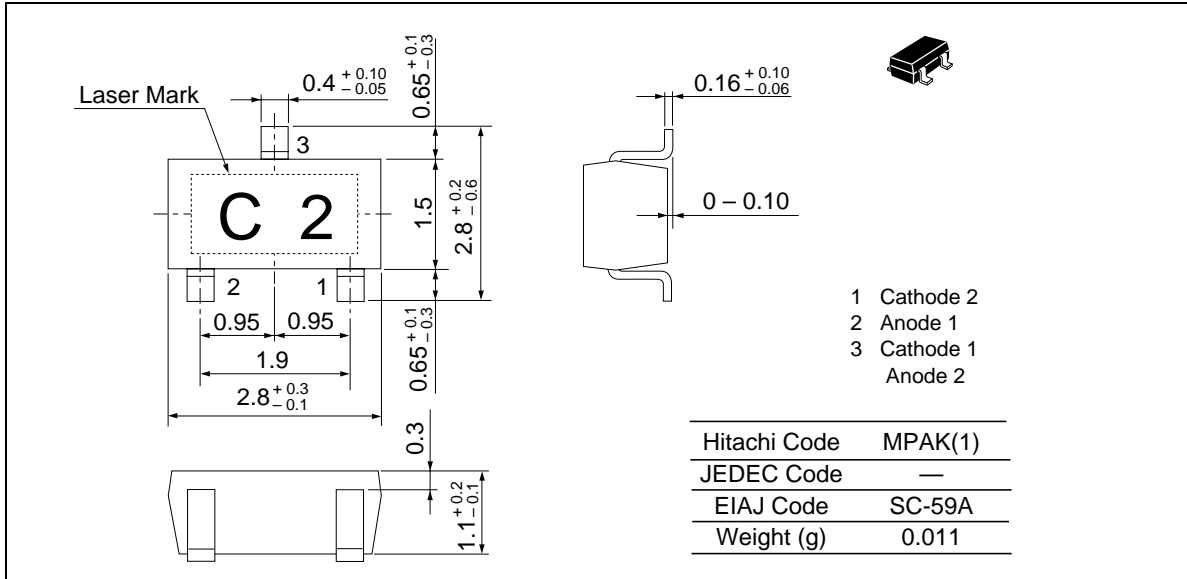


Fig.3 Capacitance Vs. Reverse voltage

# HSM276S

## Package Dimensions

Unit : mm



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